AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A phosphor element comprising:

a pair of electrodes opposed to each other; and

a phosphor layer disposed between the pair of electrodes and having silicon fine particles whose average particle diameter is not more than 100 nm,

wherein at least a part of each surface of substantially all of the silicon fine particles is covered with a conductive material film.

2. (Currently Amended) The phosphor element according to claim 1, wherein the conductive material film comprises an oxide or a composite oxide containing at least one element selected from a group of indium, tin, zinc, and gallium.

3. (Currently Amended) The phosphor element according to claim 1, wherein the conductive material film comprises a nitride or a composite nitride containing at least one element selected from a group of titanium, zirconium, hafnium, gallium, and aluminum.

4. (Currently Amended) The phosphor element according to claim 1, wherein the conductive material film is titanium nitride whose thickness is not more than 30 nm.

5. (Currently amended) The phosphor element according to claim 1, wherein the conductive material film is magnesium silver alloy whose thickness is not more than 50 nm.

6. (Previously Presented) The phosphor element according to claim 1, further comprising an electron transport layer between the phosphor layer and at least one of the electrodes.

7. (Previously Presented) The phosphor element according to claim 1, further comprising a thin film transistor connected to at least one of the electrodes.

8. (Currently Amended) A display device comprising:

a two-dimensional phosphor element array in which the phosphor elements are arranged, each phosphor element comprising:

a pair of electrodes opposed to each other;

a phosphor layer disposed between the pair of electrodes and having silicon fine particles whose average particle diameter is not more than 100 nm, wherein at least a part of each surface of substantially all of the silicon fine particles is covered with a conductive material film; and

a thin film transistor connected to at least one of the electrodes;

a plurality of x electrodes extending parallel to each other in a first direction which is parallel to a surface of the phosphor element array; and

a plurality of y electrodes extending parallel to each other in a second direction which is perpendicular to the surface of the phosphor element array, and

wherein the thin film transistor of the phosphor element array connects the x electrode to the y electrode.

9. (Currently Amended) A phosphor element, comprising:

a pair of electrodes opposed to each other; and

a phosphor layer disposed between the pair of electrodes and having silicon fine particles, the silicon fine particles having average particle diameter of not more than 100nm and disposed at least at non-edge positions within the phosphor layer,

wherein at least a part of each surface of substantially all of the silicon fine particles is covered with a conductive material film ~~a surface of the silicon fine particle is covered with a conductive material~~.